

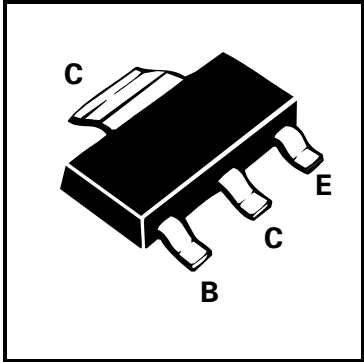
# SOT223 NPN SILICON PLANAR MEDIUM POWER DARLINGTON TRANSISTOR

FZT603

ISSUE 3 – NOVEMBER 1995

## FEATURES

- \* 2A continuous current
- \* Useful  $h_{FE}$  up to 6A
- \* Fast Switching



PARTMARKING DETAIL – DEVICE TYPE IN FULL

## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	100	V
Collector-Emitter Voltage	$V_{CEO}$	80	V
Emitter-Base Voltage	$V_{EBO}$	10	V
Peak Pulse Current	$I_{CM}$	6	A
Continuous Collector Current	$I_C$	2	A
Power Dissipation	$P_{tot}$	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	°C

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	100	240		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80	110		V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10	16		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$			0.01 10	$\mu\text{A}$ $\mu\text{A}$	$V_{CB}=80\text{V}$ $V_{CB}=80\text{V}, T_{amb}=100^\circ\text{C}$
Emitter Cut-Off Current	$I_{EBO}$			0.1	$\mu\text{A}$	$V_{EB}=8\text{V}$
Collector Cut-Off Current	$I_{CES}$			10	$\mu\text{A}$	$V_{CES}=80\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.79 0.80 0.88 0.99 0.86	0.88 0.90 1.00 1.13	V V V V V	$I_C=0.25\text{A}, I_B=0.25\text{mA}^*$ $I_C=0.4\text{A}, I_B=0.4\text{mA}^*$ $I_C=1\text{A}, I_B=1\text{mA}^*$ $I_C=2\text{A}, I_B=20\text{mA}^*$ $I_C=2\text{A}, I_B=20\text{mA} \dagger$

†  $T_j=150^\circ\text{C}$



# FZT603

## ELECTRICAL CHARACTERISTICS (Continued)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.7	1.95	V	$I_C=2A, I_B=20mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		1.5	1.75	V	$I_C=2A, V_{CE}=5V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	3k 5k 3k 2k	14k 15k 14k 10k 2k 750	100k		$I_C=50mA, V_{CE}=5V^*$ $I_C=500mA, V_{CE}=5V^*$ $I_C=1A, V_{CE}=5V^*$ $I_C=2A, V_{CE}=5V^*$ $I_C=5A, V_{CE}=5V^*$ $I_C=6A, V_{CE}=5V^*$
Transition Frequency	$f_T$	150			MHz	$I_C=100mA, V_{CE}=10V$ $f=20MHz$
Output Capacitance	$C_{ibo}$		90		pF	$V_{EB}=500mV, f=1MHz$
Output Capacitance	$C_{obo}$		15		pF	$V_{CB}=10V, f=1MHz$
Switching Times	$t_{on}$		0.5		$\mu s$	$I_C=0.5A, V_{CE}=10V$ $I_{B1}=I_{B2}=0.5mA$
	$t_{off}$		1.6		$\mu s$	

\*Measured under pulsed conditions. Pulse width=300ms. Duty cycle  $\leq 2\%$   
 Spice parameter data is available upon request for this device

# FZT603

## TYPICAL CHARACTERISTICS

